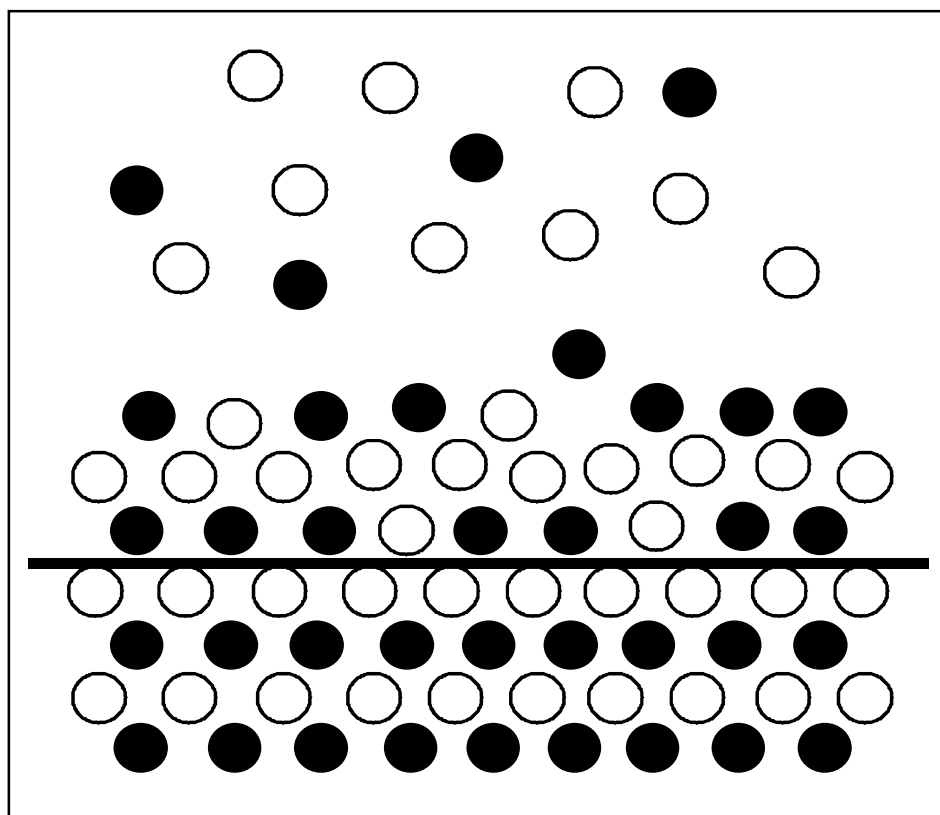


4th Symposium On Non-Stoichiometric III-V Compounds

Program



2nd – 4th October 2002

**Asilomar Conference Grounds
Pacific Grove, California**

PROGRAM

Opening Session Wed 08:30-10:15

(Chair: John Whitaker)

08:30 Welcome to Asilomar

T. R. Weatherford

08:45 Call it Non-Stoichiometric GaAs, not LT GaAs: A Look Back and a Look Forward on this Subject (invited)

G. L. Witt

09:15 Arsenic Interstitials in As-rich GaAs: Can they be Important and if so, When?

C. G. Morgan, J. T. Schick, and P. Papoulias

09:45 Increased Interstitial As Concentration in GaAs Layers Grown at Low Temperature on <111>A Misoriented GaAs(001) Substrate

C. Schuer, T. Riedl, T. Marek and H.P. Strunk

Session 2 Wed 10:35-12:05

(Chair: Gerald Witt)

10:35 Effects of Stoichiometry on Point Defects and Impurities in GaN (invited)

C.G. Van de Walle

11:05 Arsenic Antisite and Nitrogen Incorporation in GaAsN grown at Low Temperature by Molecular Beam Epitaxy

R. Zhao, J. Gebauer, P. Specht, E. R. Weber

11:35 Vacancies as optically and electrically active defects in III-nitrides and III-arsenides (invited)

K. Saarinen

12:05 lunch break

Session 3 Wed 13:30-15:30 (*Chair: Takashi Inushima*)

13:30 Defect Structure of GaN Epilayers: M-plane versus C-plane growth (invited)

A. Trampert

14:00 Characteristics of III-Nitride Films Grown by Electron Cyclotron Resonance Plasma-Assisted MBE and its Stoichiometric Control under plasma growth process (invited)

T. Yodo

14:30 Role of Carbon in Silicon-doped GaN Grown by Metalorganic Chemical Vapor Deposition

C.H. Seager, A.F. Wright, W. Goetz, T. Mihopoulos, J. Yu

15:00 Influence of Carbon Doping on the Optical and Electrical Properties of MBE GaN Grown on MOVPE-GaN / Sapphire Templates

R. Armitage, Q. Yang, H. Feick, and E.R. Weber

Session 4 Wed 15:50-17:20 (*Chair: Christian Kisielowski*)

15:50 Mechanism of Laser Lift-off in GaN

E.A. Stach, T. Sands, J.A. Schroeder, Y. Cho, W.S. Wong, M. Kneissl

16:20 Growth of Thin Oriented Gallium Nitride Films on Amorphous Substrates Using Self-Assembly

M.K. Sunkara and H. Li

16:50 Superconducting Characteristics of InN Grown on Sapphire (0001) (invited)

T. Inushima, S. Takenobu, M. Motokawa, A. Yamamoto, Y. Saitoh, Y. Nanishi

18:30 Social Event on Cannery Row

Session 5 Thu 08:15-10:15 (Chair: Wolfgang Jaeger)

08:15 On the Feasibility to Investigate Point Defects by Advanced Electron Microscopy (invited)

C. Kisielowski

08:45 Non-Stoichiometry at Threading Dislocations in GaN

I. Arslan, N.D. Browning

09:15 Comparison of $\text{Al}_x\text{Ga}_{1-x}\text{N}$ Films Grown on Sapphire by MBE under N-rich and Metal-rich Conditions

J. Jasinski, Z. Liliental-Weber, L. He, M. A. Reshchikov, H. Morkoç

09:45 Desorption Induced Defect Formation in GaN (invited)

E.A. Stach, W.S. Wong, M. Kneissl

Session 6 Thu 10:35-12:05 (Chair: Chris Van de Walle)

10:35 Photoconductivity of GaN Thin Layers

A. Castaldini, A. Cavallini, L. Polenta

11:05 Doping and Deep Level Defects in High Al Content AlGa_N

S.T. Bradley, P.E. Smith, L.J. Brillson, W.J. Schaff

11:35 Low Frequency Noise Characterization of Semiconductors
(invited)

M.J. Cich, S.Y. Tzeng, and E. R. Weber

12:05 lunch break

Session 7 Thu 13:30-15:30

(Chair: Peter Kiesel)

13:30 Dopant Induced Non-Stoichiometry Effects in III-V Semiconductors (invited)

W. Jaeger, C. Jaeger

14:00 Highly Doped n-LT-(Al)GaAs Layers

S. Malzer, C. Steen and G.H. Döhler

14:30 The Role of Non-Stoichiometric III-Vs in Radiation Hardened Devices

T. R. Weatherford, Q. Yang, E.R. Weber

09:45 Nuclear Radiation Effects on GaAs and GaN Thin Films and Devices (invited)

S.M. Khanna

Plenary Discussion Thu 16:00-17:00

“Future Stoichiometry-Related Research Goals for III-Nitrides: Engineering Useful Defects”

Harry Dietrich, Office of Naval Research

Karen Moore, Motorola Labs

Eicke R. Weber, University of California, Berkeley

18:00 BBQ dinner

PROGRAM OVERVIEW

Wednesday	Oct. 2nd	Thursday	Oct. 3rd	Friday	Oct. 4th
08:30	Welcome	08:15	C. Kisielowski	08:15	P. Specht
08:45	G.L. Witt	08:45	I. Arslan	08:45	C. Steen
09:15	C.G. Morgan	09:15	J. Jasinski	09:15	M. Mikulics
09:45	C. Schuer	09:45	E.A. Stach	09:45	Coffee Break
10:15	Coffee Break	10:15	Coffee Break	09:45	Coffee Break
10:35	C.G. Van de Walle	10:35	L. Polenta	10:05	T. Okuno
11:05	R. Zhao	11:05	S.T. Bradley	10:35	F. Renner
11:35	K. Saarinen	11:35	M.J. Cich	11:05	F. Dubecky
12:05	Lunch	12:05	Lunch	11:35	Closing Remarks
13:30	A. Trampert	13:30	W. Jaeger	11:50	Lunch
14:00	T. Yodo	14:00	S. Malzer		
14:30	W. Goetz	14:30	T.R. Weatherford		
15:00	R. Armitage	15:00	S.M. Khanna		
15:30	Coffee Break	15:30	Coffee Break		
15:50	E.A. Stach	16:00	Plenary Discussion		
16:20	M.K. Sunkara		H. Dietrich, K. Moore, E.R. Weber		
16:50	T. Inushima				
18:30	Cannery Row Social	18:00	BBQ Dinner		

